



MICROWAVE CORPORATION v03.1109



HMC490LP5 / 490LP5E

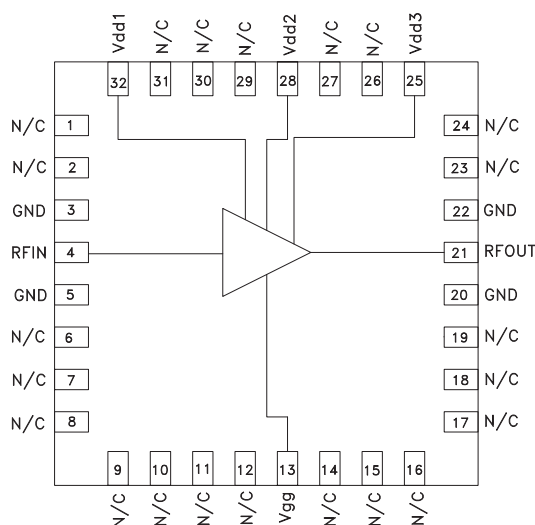
**GaAs PHEMT MMIC LOW NOISE
HIGH IP3 AMPLIFIER, 12 - 16 GHz**

Typical Applications

The HMC490LP5(E) is ideal for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios
- VSAT
- Military EW, ECM & C³I

Functional Diagram



Features

- Noise Figure: 2.5 dB
- P1dB Output Power: +25 dBm
- Gain: 23 dB
- Output IP3: +34 dBm
- +5V Supply
- 50 Ohm Matched Input/Output
- 32 Lead 5x5mm SMT Package: 25mm²

General Description

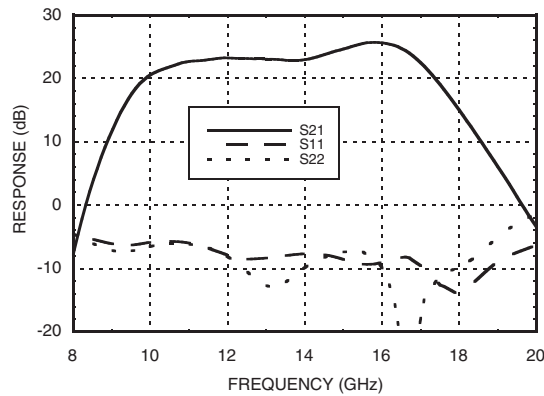
The HMC490LP5(E) is a high dynamic range GaAs PHEMT MMIC Low Noise Amplifier which operates between 12 and 16 GHz. The HMC490LP5(E) provides 23 dB of gain, 2.5 dB noise figure and an output IP3 of +34 dBm from a +5V supply voltage. This versatile amplifier combines excellent, stable +25 dBm P1dB output power with very low noise figure making it ideal for receive and transmit applications. The amplifier is packaged in a leadless 5x5 mm QFN surface mount package.

Electrical Specifications, $T_A = +25^\circ\text{C}$, $V_{dd} = 5\text{V}$, $I_{dd} = 200\text{mA}$ *

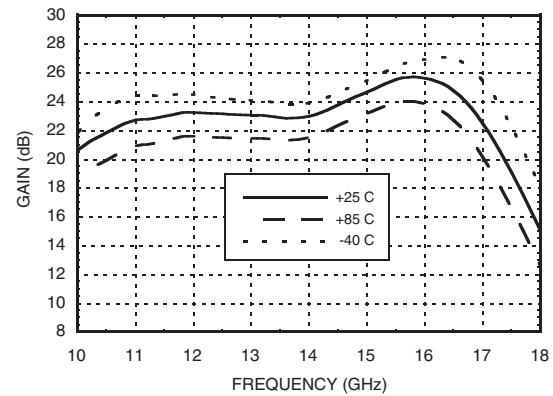
Parameter	Min.	Typ.	Max.	Units
Frequency Range	12 - 16			GHz
Gain	20	23		dB
Gain Variation Over Temperature		0.03	0.04	dB/°C
Noise Figure		2.5	3.5	dB
Input Return Loss		8		dB
Output Return Loss		8		dB
Output Power for 1 dB Compression (P1dB)	22	25		dBm
Saturated Output Power (Psat)		27		dBm
Output Third Order Intercept (IP3)		34		dBm
Supply Current (Idd)(Vdd = 5V, Vgg = -0.8V Typ.)		200		mA

* Adjust Vgg between -2 to 0V to achieve Idd = 200 mA typical.

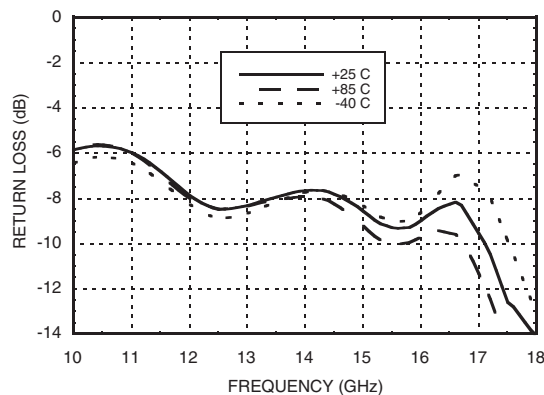
Broadband Gain & Return Loss



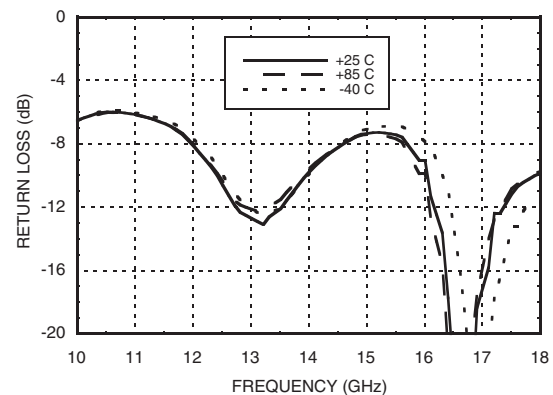
Gain vs. Temperature



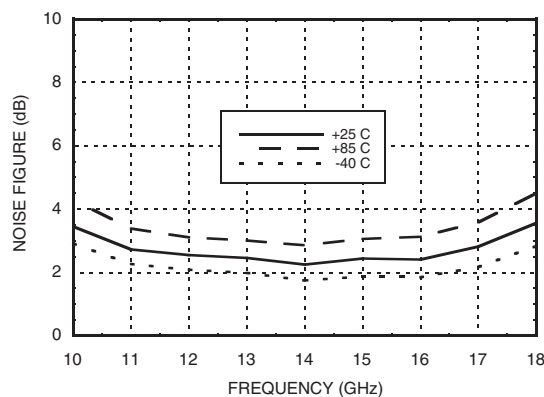
Input Return Loss vs. Temperature



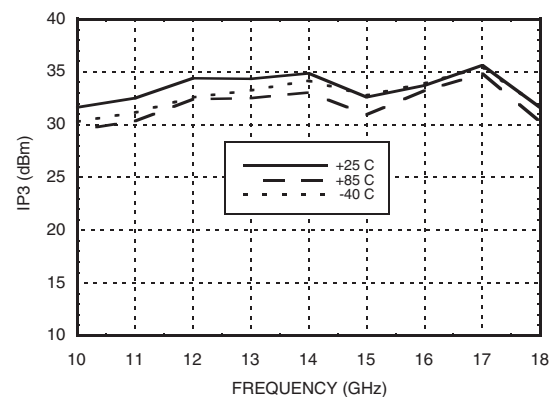
Output Return Loss vs. Temperature



Noise Figure vs. Temperature



Output IP3 vs. Temperature





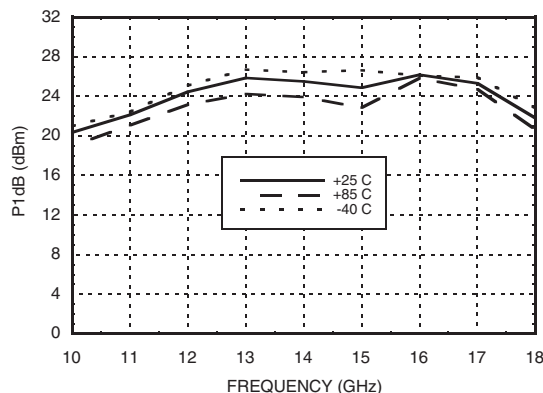
MICROWAVE CORPORATION v03.1109



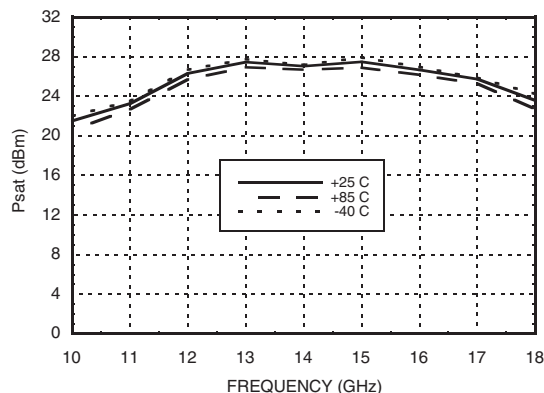
HMC490LP5 / 490LP5E

**GaAs PHEMT MMIC LOW NOISE
HIGH IP3 AMPLIFIER, 12 - 16 GHz**

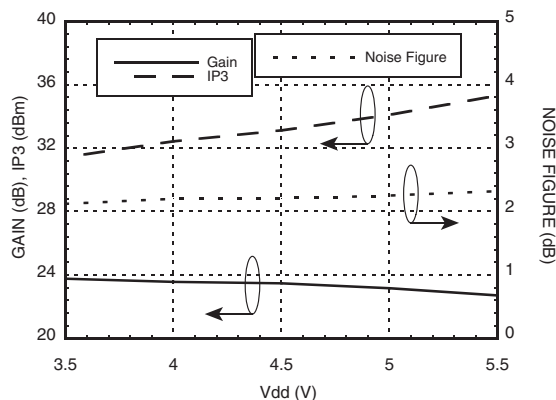
P1dB vs. Temperature



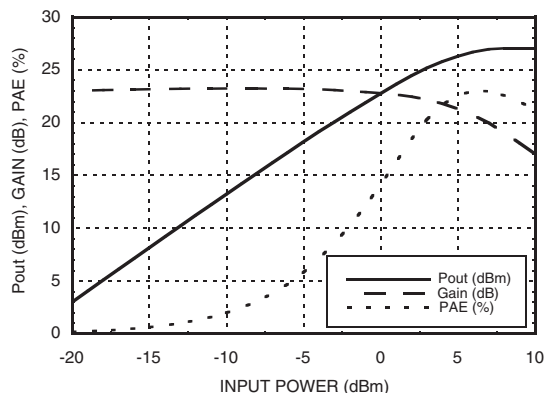
Psat vs. Temperature



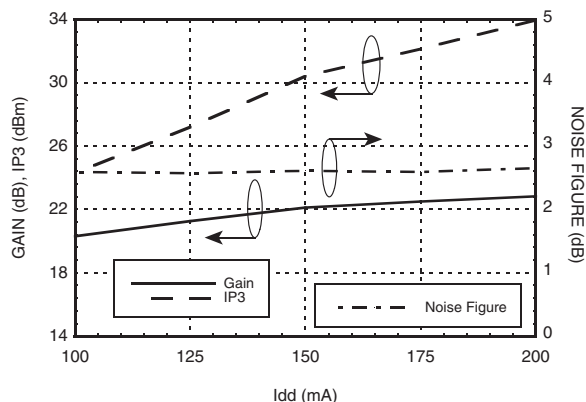
**Gain, Noise Figure & OIP3 vs.
Supply Voltage @ 14 GHz, Idd= 200 mA**



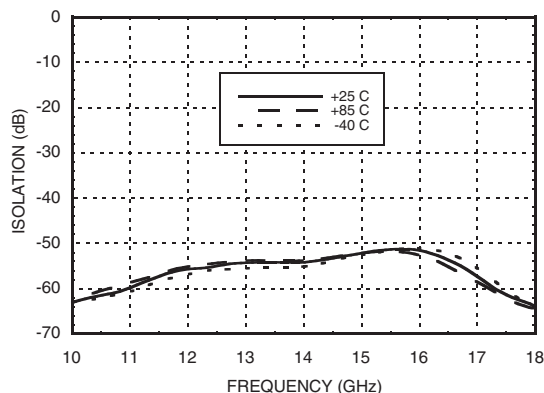
Power Compression @ 14 GHz



**Gain, Noise Figure & IP3 vs.
Supply Current @ 14 GHz, Vdd= 5V***



Reverse Isolation vs. Temperature



* Idd is controlled by varying Vgg



MICROWAVE CORPORATION v03.1109



HMC490LP5 / 490LP5E

**GaAs PHEMT MMIC LOW NOISE
HIGH IP3 AMPLIFIER, 12 - 16 GHz**

Absolute Maximum Ratings

Drain Bias Voltage (Vdd1, Vdd2, Vdd3)	+5.5V
Gate Bias Voltage (Vgg)	-4 to 0V
RF Input Power (RFIN)(Vdd = +5V)	+10 dBm
Channel Temperature	175 °C
Continuous P _{diss} (T = 85 °C) (derate 29 mW/°C above 85 °C)	2.65 W
Thermal Resistance (channel to ground paddle)	34 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C

Typical Supply Current vs. Vdd

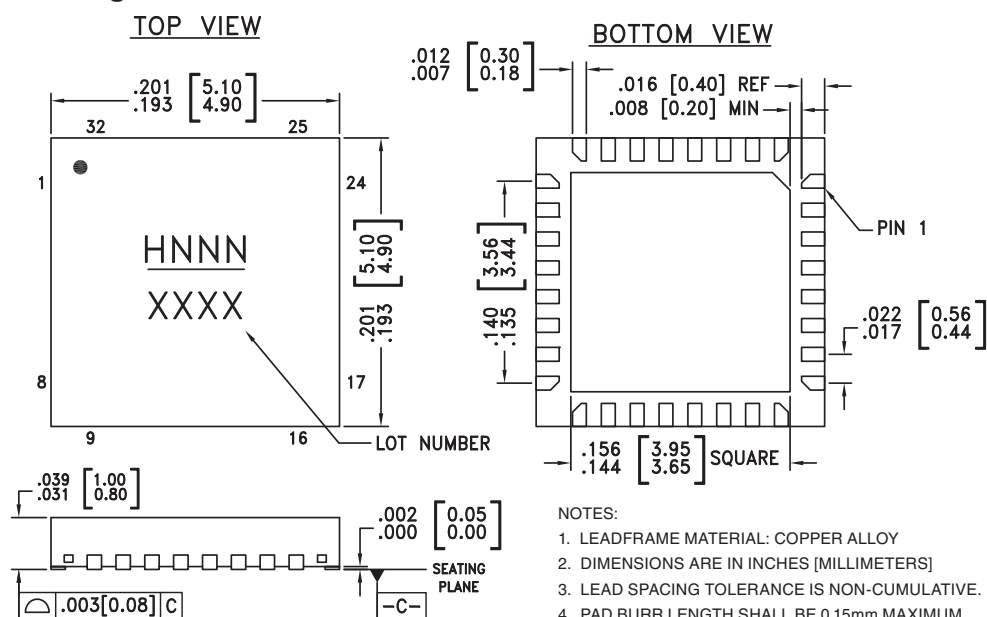
Vdd (V)	I _{dd} (mA)
+3.0	140
+3.5	154
+4.0	168
+4.5	188
+5.0	200
+5.5	208

Note: Amplifier will operate over full voltage ranges shown above.



**ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS**

Outline Drawing



Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[3]
HMC490LP5	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 ^[1]	H490 XXXX
HMC490LP5E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 ^[2]	H490 XXXX

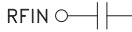
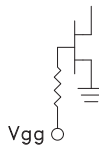
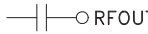
[1] Max peak reflow temperature of 235 °C

[2] Max peak reflow temperature of 260 °C

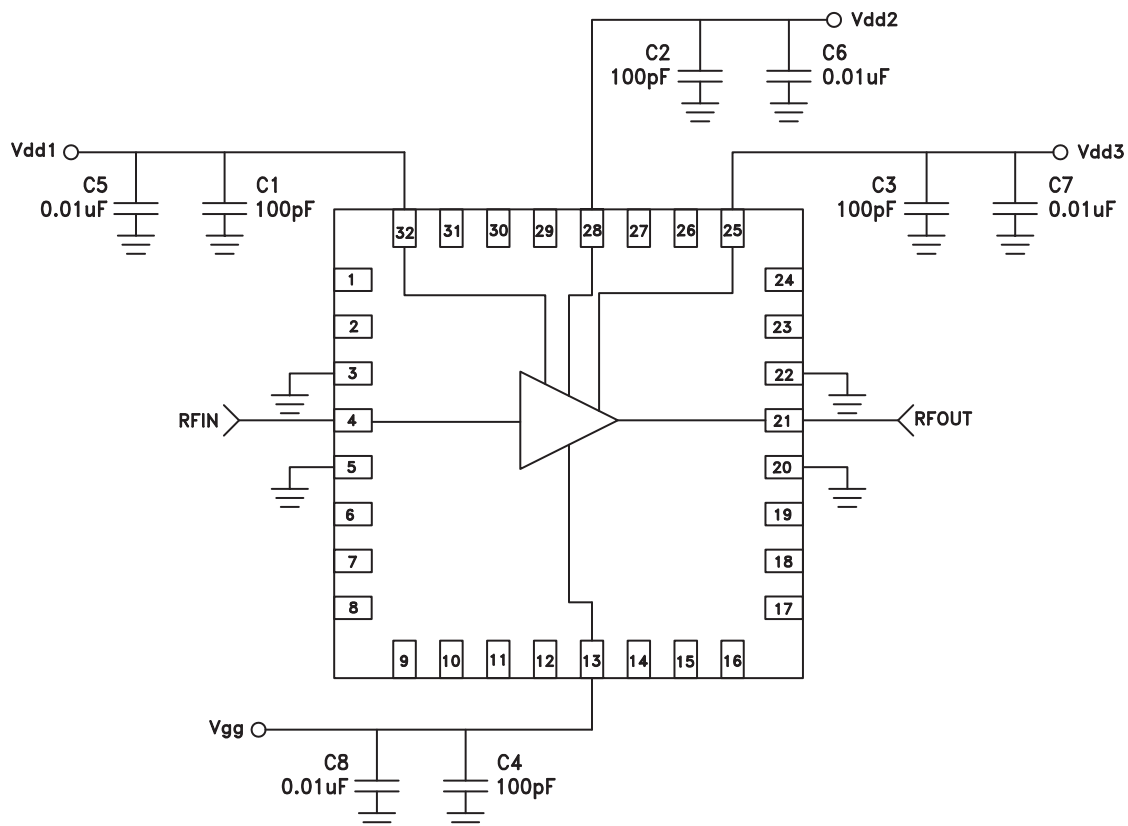
[3] 4-Digit lot number XXXX

For price, delivery, and to place orders, please contact Hittite Microwave Corporation:
20 Alpha Road, Chelmsford, MA 01824 Phone: 978-250-3343 Fax: 978-250-3373
Order On-line at www.hittite.com

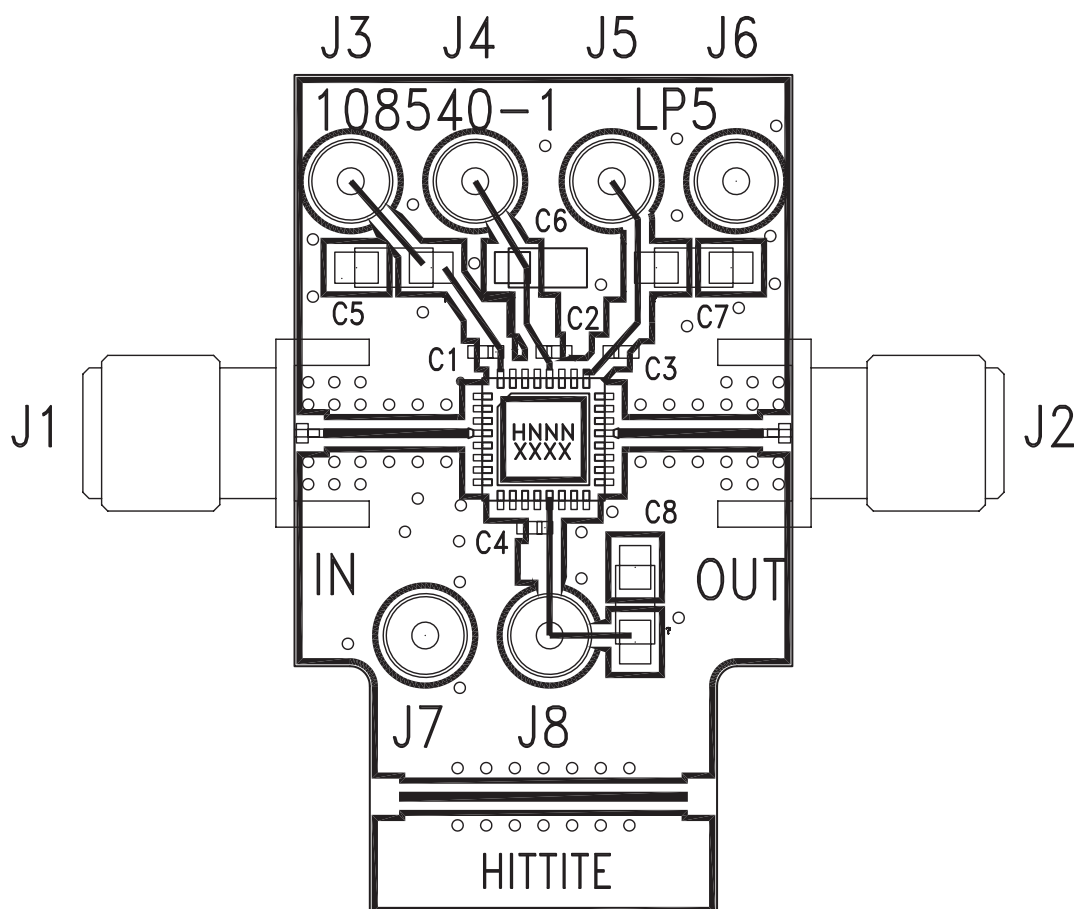
Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 2, 6 - 12, 14 - 19, 23, 24, 26, 27, 29 - 31	N/C	The pins are not connected internally; however, all data shown herein was measured with these pins connected to RF/DC ground externally.	
3, 5, 20, 22	GND	Package bottom must also be connected to RF/DC ground.	
4	RFIN	This pad is AC coupled and matched to 50 Ohms.	
13	Vgg	Gate control for amplifier. Adjust to achieve I _{dd} of 200 mA. Please follow "MMIC Amplifier Biasing Procedure" Application Note. External bypass capacitors of 100 pF and 0.01 µF are required.	
21	RFOUT	This pad is AC coupled and matched to 50 Ohms.	
25, 28, 32	Vdd3, 2, 1	Power Supply Voltage for the amplifier. External bypass capacitors of 100 pF and 0.01 µF are required.	

Application Circuit



Evaluation PCB



List of Materials for Evaluation PCB 108402 ^[1]

Item	Description
J1 - J2	PCB Mount SMA Connector
J3 - J8	DC Pin
C1 - C4	1000 pF Capacitor, 0402 Pkg.
C5 - C8	4.7 μ F Capacitor, Tantalum
U1	HMC490LP5 / HMC490LP5E
PCB ^[2]	108540 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9